



### 20V N-Channel Enhancement Mode MOSFET

Voltage

20 V

Current

570mA

#### **Features**

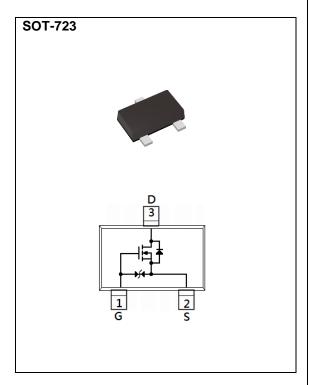
- Advanced Trench Process Technology
- ESD Protected
- Specially Designed for Switch Load, PWM Application, etc
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

• Case : SOT-723 Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.00005 ounces, 0.0013 grams



## **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS		
Drain-Source Voltage		V <sub>DS</sub>	20	V	
Gate-Source Voltage		V <sub>GS</sub>	±8		
Continuous Drain Current(Note 4)		I <sub>D</sub>	570	mA	
Pulsed Drain Current <sup>(Note 1)</sup>		I <sub>DM</sub>	1200		
Power Dissipation	T <sub>A</sub> =25°C	Po	150	mW	
	Derate above 25°C		1.2	mW/°C	
Operating Junction and Storage Temperature Range		T <sub>J</sub> ,T <sub>STG</sub>	-55~150	°C	
Typical Thermal Resistance - Junction to Ambient <sup>(Note 5)</sup>		R <sub>0</sub> JA	833	°C/W	





## Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	20	-	-		
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	0.3	0.68	1.0	V	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =500mA	-	200	300		
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =400mA	-	240	400	mΩ	
		V <sub>GS</sub> =1.8V, I <sub>D</sub> =200mA	-	300	550		
		V <sub>GS</sub> =1.5V, I <sub>D</sub> =100mA	-	370	800		
		V <sub>GS</sub> =1.2V, I <sub>D</sub> =10mA	-	680	1500		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V	-	-	1	uA	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V	-	-	±10		
Dynamic <sup>(Note 6)</sup>							
Total Gate Charge	Qg	V <sub>DS</sub> =16V, I <sub>D</sub> =500mA, V <sub>GS</sub> =4.5V <sup>(Note 2,3)</sup>	-	1.1	-	nC	
Gate-Source Charge	Qgs		-	0.2	-		
Gate-Drain Charge	$Q_{gd}$	VGS=4.5 V(Note 2,6)	-	0.1	-		
Input Capacitance	Ciss		-	50	-	pF	
Output Capacitance	Coss	V <sub>DS</sub> =16V, V <sub>GS</sub> =0V, f=1MHZ	-	12	-		
Reverse Transfer Capacitance	Crss	I=IIVIMZ	-	10	-		
Gate resistance	Rg	f=1.0MHZ	-	1.6	-	Ω	
Turn-On Delay Time	td <sub>(on)</sub>		-	2	-	ns	
Turn-On Rise Time	tr	V <sub>DS</sub> =16V, I <sub>D</sub> =500mA,	-	22	-		
Turn-Off Delay Time	td <sub>(off)</sub>	V <sub>GS</sub> =4.5V, R <sub>G</sub> =3.3Ω	-	57	-		
Turn-Off Fall Time	tf	(1.000 2,0)	-	34	-		
Drain-Source Diode							
Diode Forward Current	Is		-	-	570	mA	
Diode Forward Voltage	V <sub>SD</sub>	Is=500mA,V <sub>GS</sub> =0V	-	0.9	1	V	

#### Notes:

- 1.Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- $3. Repetitive\ rating,\ pulse\ width\ limited\ by\ junction\ temperature\ T_J(MAX) = 150^{\circ}C. Ratings\ are\ based\ on\ low\ frequency\ and\ duty\ cycles\ to\ keep\ initial\ T_J=25^{\circ}C.$
- 4. The maximum current rating is package limited.
- 5.ReJA is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.





#### TYPICAL CHARACTERISTIC CURVES

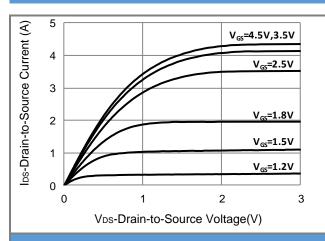


Fig.1 Output Characteristics

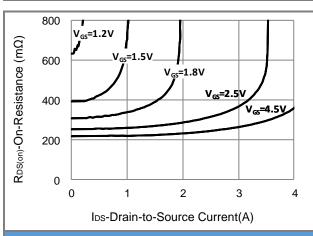


Fig.3 On-Resistance vs. Drain Current

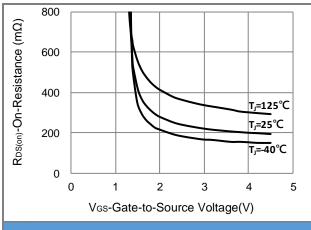


Fig.5 On-Resistance Variation with V<sub>GS</sub>

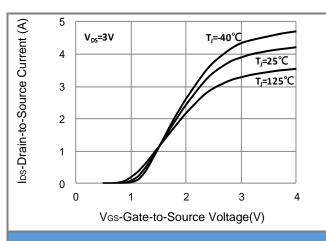


Fig.2 Transfer Characteristics

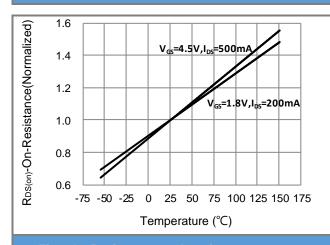


Fig.4 On-Resistance vs. Junction temperature

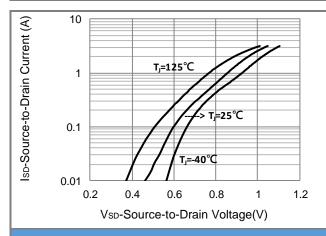


Fig.6 Source-Drain Diode Forward Voltage





### **TYPICAL CHARACTERISTIC CURVES**

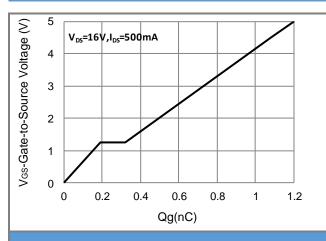


Fig.7 Gate-Charge Characteristics

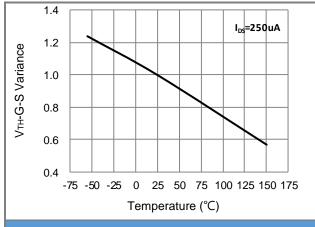


Fig.9 Threshold Voltage Variation with Temperature

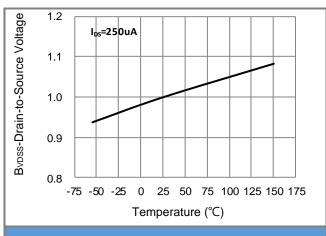


Fig.8 Breakdown Voltage Variation vs. Temperature

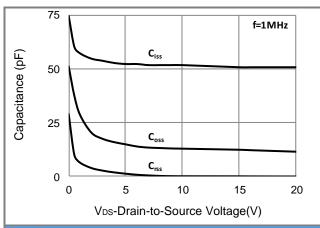


Fig.10 Capacitance vs. Drain-Source Voltage

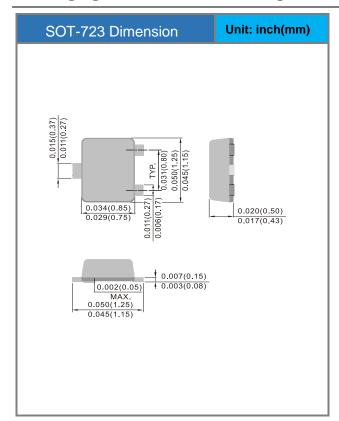


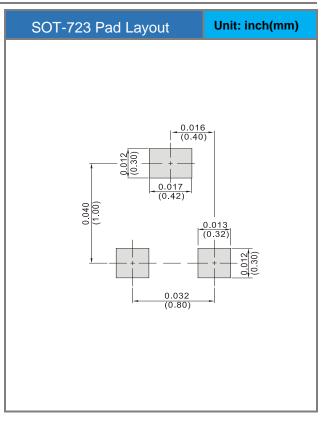


### Part No. Packing Code Version

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJV1716_R1_00301	SOT-723	8K pcs / 7" reel	16	Halogen free RoHS compliant

## **Packaging Information & Mounting Pad Layout**









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